

Kei Sumita

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Operation of (111) Ge-on-Insulator n-Channel MOSFET Fabricated by Smart-Cut Technology. IEEE Electron Device Letters, 2020, 41, 985-988. | 3.9 | 13 |
| 2 | Fabrication of thin body InAs-on-insulator structures by Smart Cut method with H ⁺ implantation at room temperature. Japanese Journal of Applied Physics, 2019, 58, SBBA03. | 1.5 | 9 |
| 3 | Effects of hydrogen ion implantation dose on physical and electrical properties of Ge-on-insulator layers fabricated by the smart-cut process. AIP Advances, 2020, 10, . | 1.3 | 7 |
| 4 | Proposal and Experimental Demonstration of Ultrathin-Body (111) InAs-On-Insulator nMOSFETs With L Valley Conduction. IEEE Transactions on Electron Devices, 2021, 68, 2003-2009. | 3.0 | 7 |
| 5 | Effective Mobility Enhancement Through Asymmetric Strain Channels on Extremely Thin Body (100) GOI pMOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 25-30. | 3.0 | 6 |
| 6 | Accurate evaluation of specific contact resistivity between InAs/Ni-InAs alloy using a multi-sidewall transmission line method. Japanese Journal of Applied Physics, 2020, 59, SGG08. | 1.5 | 5 |
| 7 | Optimum Channel Design of Extremely-Thin-Body nMOSFETs Utilizing Anisotropic Valley-Robust to Surface Roughness Scattering. IEEE Transactions on Electron Devices, 2022, 69, 2115-2121. | 3.0 | 5 |
| 8 | Influence of layer transfer and thermal annealing on the properties of InAs-On-Insulator films. Journal of Applied Physics, 2020, 128, . | 2.5 | 4 |
| 9 | Electrical Properties of Ultra-Thin Body (111) Ge-On-Insulator n-Channel MOSFETs Fabricated by Smart-Cut Process. IEEE Journal of the Electron Devices Society, 2021, 9, 612-617. | 2.1 | 3 |
| 10 | Subband Engineering by Combination of Channel Thickness Scaling and (111) Surface Orientation in InAs-On-Insulator nMOSFETs. , 2020, , . | | 3 |
| 11 | Optimum Design of Channel Material and Surface Orientation for Extremely-Thin-Body nMOSFETs under New Modeling of Surface Roughness Scattering. , 2021, , . | | 3 |
| 12 | Advanced CMOS technologies for ultra-low power logic and AI applications. , 2021, , . | | 2 |
| 13 | Evaluation of interface traps inside the conduction band of InAs-on-insulator nMOSFET by self-consistent Hall-QSCV method. Applied Physics Letters, 2021, 119, . | 3.3 | 2 |
| 14 | Corrections to "Operation of (111) Ge-on-Insulator n-channel MOSFET Fabricated by Smart-Cut Technology" [Jul 20 985-988]. IEEE Electron Device Letters, 2020, 41, 1266-1266. | 3.9 | 1 |